New Jersey Semi-Conductor Products, Inc.

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> Mesa transistor type 2N695 is a germanium P-N-P diffused junction transistor designed primarily for reliable operation in ultra high speed switching applications. Its unique structure provides the versatility required for de-pendable performance in a wide variety of computer pulse and switching circuits (both saturating and non-saturating), The internal design and hermetically sealed package enable it to meet or exceed the mechanical and environmental requirements of military specification MIL-T-19500A. The high maximum junction temperature of 100°C permits this Germanium transistor to be reliably operated in applications where Germanium transistors have not been previously considered.

ABSOLUTE MAXIMUM RATINGS

Collector to Base Voltage	15 volts
Collector to Emitter Voltage	12 volts
Emitter to Base Voltage	3 volts
Collector D.C. Current	20 ma
Maximum Junction Temperature	100°C
Maximum Storage Temperature	100°C
Collector Dissipation in Free Air Derate 1.0 mw/°C above 50°C	50 mw

ELECTRICAL CHARACTERISTICS

@ 25°C unless otherwise noted	typ.	max.	UNITS
Collector Cutoff Current, Ico Vos = -6V, In = 0	1	10	μ a
Emitter Cutoff Current, I_{E0} $V_{EB} = -2V$, $I_{C} = 0$	10	_	μа
Collector to Emitter Voltage, V_{CE} $I_C = 10 \text{ ma}, I_E = 1 \text{ ma}$.25		volts
Emitter to Base Voltage, V_{EB} $I_C = 10$ ma, $I_B = 1$ ma	.35		volts
Forward Transfer Current Ratio, hre lc = 10 ma, Vce = 0.5 V	30	-	
Output Capacitance, C_{ob} $V_c = -6V$, $I_E = 0$	4	_	μμf

THERMAL CHARACTERISTICS

- 1					
	Thermal Resistance	t .	1°C/mw		
	Junction to Case		,		
			1.		

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TECHNICAL DATA

2N695

ULTRA HIGH - SPEED MESA SWITCHING TRANSISTOR

August 1, 1958

- Extreme reliability only high to perature materials used, process ca fully controlled.
- Rugged withstands 50,000G acc eration.
- Low nuclear radiation susceptibili
- Meets or exceeds mechanical and vironmental requirements of MIL 19500A.
- High uniformity "normal" inste of "selected" distribution.
- New header design provides effect. interelectrode capacitance isolati ... smaller inductance.

Outline Dimensions Twice Actual Size .166 MAX DIA .173 MAX +.002 .017 -.001 DIA .500 ±.030 ±.005 .200 DIA EMITTER 132 MAX -BASE XAM 250. SHIELD COLLECTOR



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice Information turnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders